

8' cont.
a recombination center formed around the partially distorted portion, the recombination center having a relatively low degree of crystallization among crystal semiconductor films forming the channel region.--

REMARKS

Claims 1-19 are pending. Claims 8-12 and 19 have been previously withdrawn from consideration. By this Amendment, the drawings are corrected pursuant to the attached Request for Approval of Drawing Correction and claim 19 is added.

Reconsideration based on the following remarks is respectfully requested.

I. The Drawings Satisfy All Formal Requirements

The Office Action objects to the drawings based on informalities. The drawings are corrected pursuant to the attached Request for Approval of Drawing Correction. Withdrawal of the objection to the drawings is respectfully requested.

II. The Specification Satisfies All Formal Requirements

The Office Action objects to the specification based on informalities. Specifically, the Office Action asserts that a section of page 12 is missing. This assertion is respectfully traversed. Page 12 of the specification is complete.

The Office Action also indicates that proper headings should be used in the specification. The substitute specification filed with the December 11, 2001 Supplemental Preliminary Amendment contains proper headings.

Withdrawal of the objection to the specification is respectfully requested.

III. The Claims Define Patentable Subject Matter

The Office Action rejects claim 1-5 and 13-17 under 35 U.S.C. §102(b) over Suzuki et al.(JP 10-79513); claim 1 under 35 U.S.C. §102(e) over Deane et al. (U.S. Patent No. 6,064,091); claims 1-7 and 13-17 under 35 U.S.C. §102(e) over Nakaoka et al. (U.S. Patent